MAAP-011161

4 W Power Amplifier
7.1 - 7.9 GHz

Rev. V1

Features

- 22.0 dB Small Signal Gain
- 46.5 dBm Third Order Intercept Point (OIP3)
- >36.5 dBm Saturated Output Power (P_{SAT})
- Bias 2000 mA at 8 V
- Lead-Free 7mm Copper Coin Air Cavity Package
- RoHS* Compliant

Description

The MAAP-011161 is a packaged linear power amplifier that operates from 7.1 - 7.9 GHz. The device provides 22 dB gain and 46.5 dBm Output Third Order Intercept Point (OIP3) with >35.5 dBm saturated output power (P_{SAT}).

The packaged amplifier comes in an air cavity 7 mm surface mount package with a copper coin paddle and is comprised of a two stage power amplifier MMIC. The device includes on-chip ESD protection structures and DC by-pass capacitors to ease the implementation and volume assembly of the packaged part.

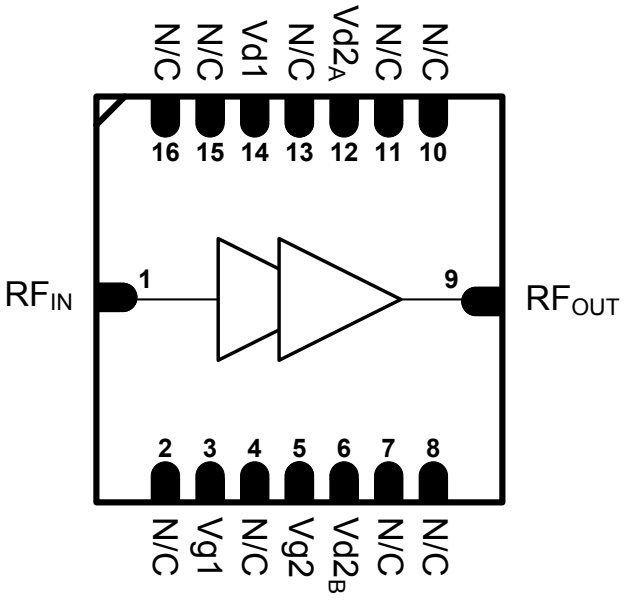
The device is specifically designed for use in 7 GHz point-to-point radios for cellular backhaul applications.

Ordering Information[1]

Part Number	Package
MAAP-011161	Bulk Quantity
MAAP-011161-TR0500	500 Piece Reel
MAAP-011161-001SMB	Sample Board

1. Reference Application Note M513 for reel size information.

Functional Schematic



Pin Configuration[3]

Pin No.	Function	Pin No.	Function
1	RF Input	9	RF Output
2	No Connection	10	No Connection
3	Gate Stg1 Bias	11	No Connection
4	No Connection	12[2]	Drain Stg2 Bias
5	Gate Stg2 Bias	13	No Connection
6[2]	Drain Stg2 Bias	14	Drain Stg1 Bias
7	No Connection	15	No Connection
8	No Connection	16	No Connection

2. Drain 2 Bias can be connected from either pins 6 or 12
3. The exposed pad centered on the package bottom must be connected to RF and DC ground.

* Restrictions on Hazardous Substances, European Union Directive 2011/65/EU.

Electrical Specifications: Freq. = 7.1 - 7.9 GHz, V_D = 8 V, I_{DQ}[4] = 2000 mA, T_A = +25°C

Parameter	Units	Min.	Typ.	Max.
Small Signal Gain	dB	18.5	22	23.5
Input Return Loss	dB	—	12	—
Output Return Loss	dB	7	12	—
Power at 1dB Gain Compression, P1dB	dB	—	35.5	—
Power at 3dB Gain Compression, P3dB	dBm	—	36	—
Saturated Output Power, P_{SAT}	dBm	35.5	36.5	—
Output IP3, 25.5 dBm SCL @ Freq = 7.5 GHz	dBm	44.5	46.5	—
Drain Bias voltage	V	—	8.0	—
Drain Current	mA	—	2000	—
Gate Voltage	V	-1.5	—	-0.5

4. Adjust V_{G1} and V_{G2} between –1.2 and –0.7V to achieve specified I_{DQ} (I_{DQ}=I_{D1}+I_{D2}). V_{G1} and V_{G2} should be the same voltage.

Absolute Maximum Ratings[5,6,7]

Parameter	Absolute Max.
Input Power	18 dBm
Drain Voltage (V_D1,2)	+9 V
Gate Voltage (V_G1,2)	-3 V
Continuous Power Dissipation @ 85ºC	33.3 W
Junction Temperature (max.)	+175ºC
Junction Temperature	+150°C
Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +150°C

5. Exceeding any one or combination of these limits may cause permanent damage to this device.
6. MACOM does not recommend sustained operation near these survivability limits.
7. Operating at nominal conditions with $T_J \leq 150°C$ will ensure MTTF > 1 x 10^6 hours. Channel temperature should be kept as low as possible to maximize lifetime.

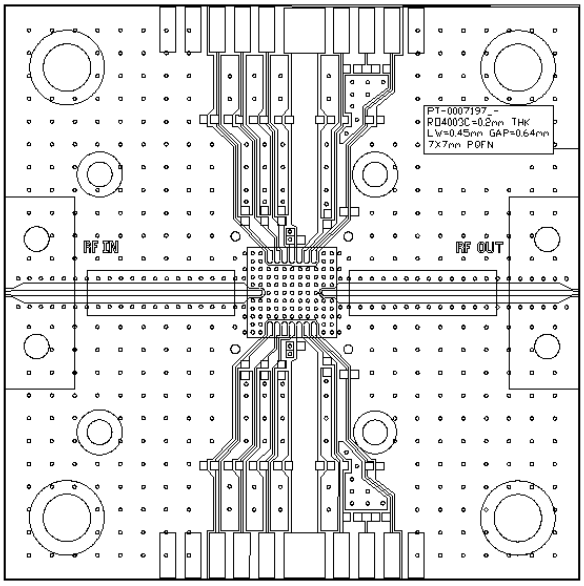
Handling Procedures

Please observe the following precautions to avoid damage:

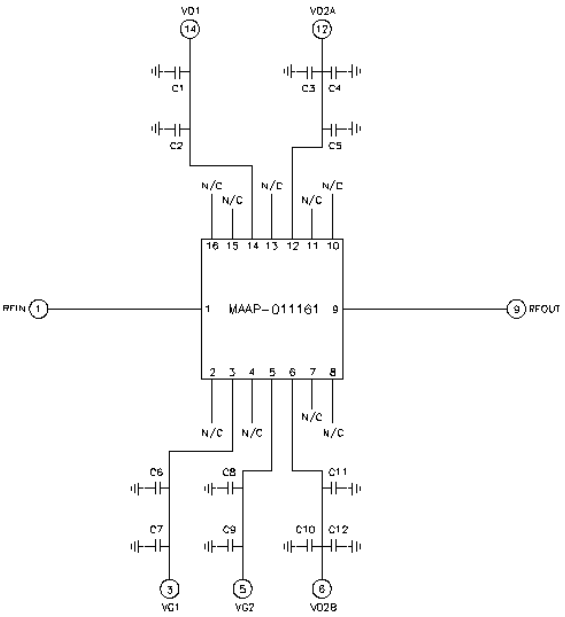
Static Sensitivity

Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these Class 1A HBM devices.

Recommended PCB Layout



Schematic

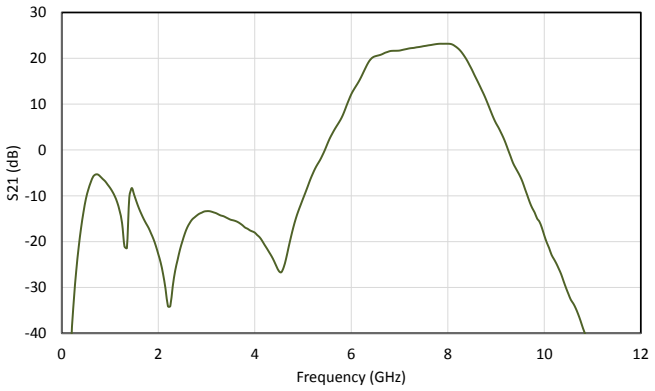


Parts List

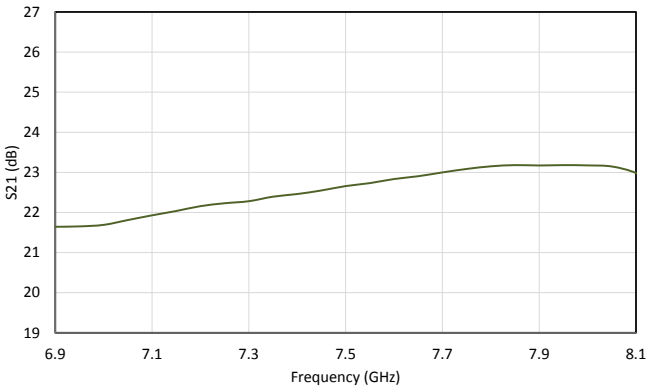
Component	Value	Package
C1, C4, C7, C9, C12	2.2 µF	0603
C3, C10	0.47 µF	0603
C2, C5, C6, C8, C11	1.0 nF	0603

Typical Performance Curves: V_D = 8 V, I_{DQ} = 2 A, V_G = -1.05 ~ -0.95 V, T_A = +25°C

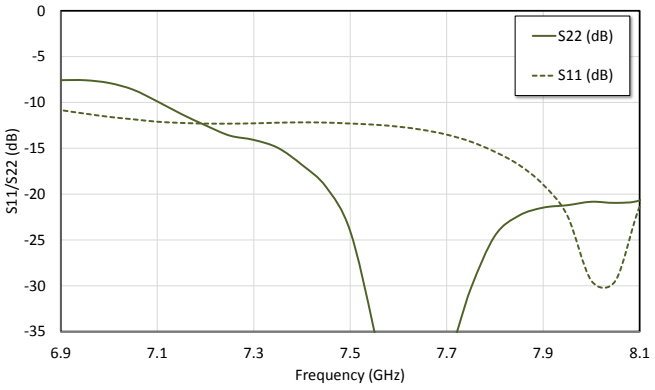
Broadband Gain (S21) vs. Freq (GHz), Vd = 8V, Id = 2A



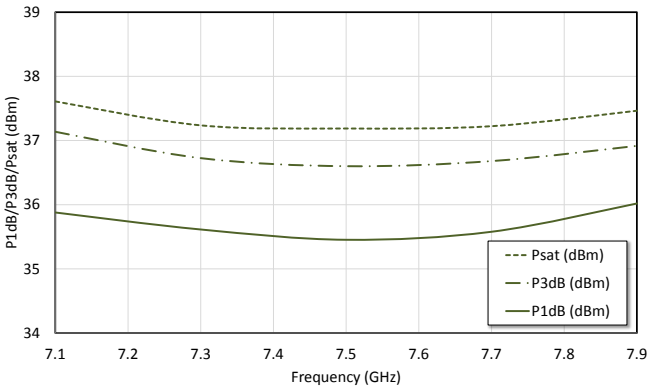
Gain (S21) vs. Freq (GHz), Vd = 8V, Id = 2A



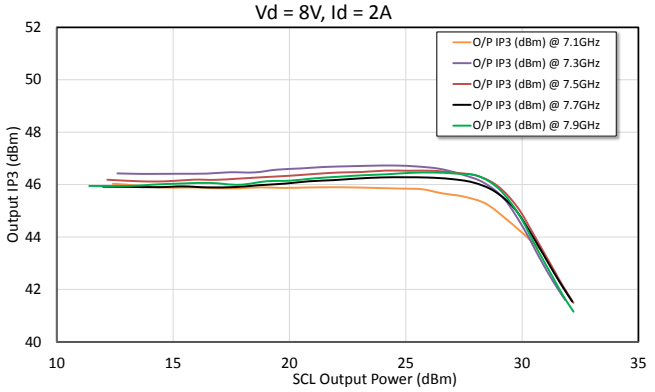
IP/OP Return Loss (S11/S22) vs. Freq (GHz), Vd = 8V, Id = 2A



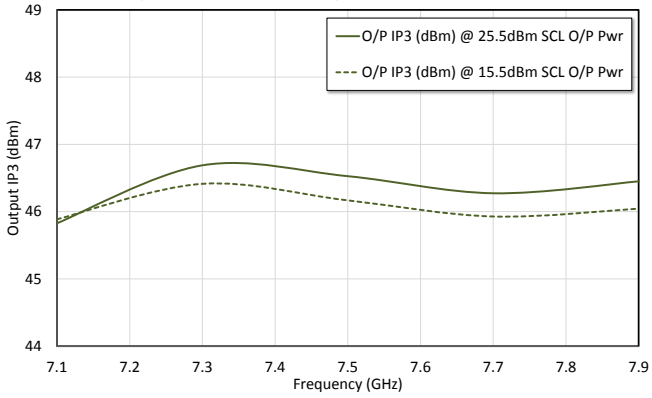
P1dB/P3dB/Psat Pwr (dBm) vs. Freq (GHz), Vd = 8V, Id = 2A



Output IP3 (dBm) vs. SCL O/P Pwr (dBm), Vd = 8V, Id = 2A

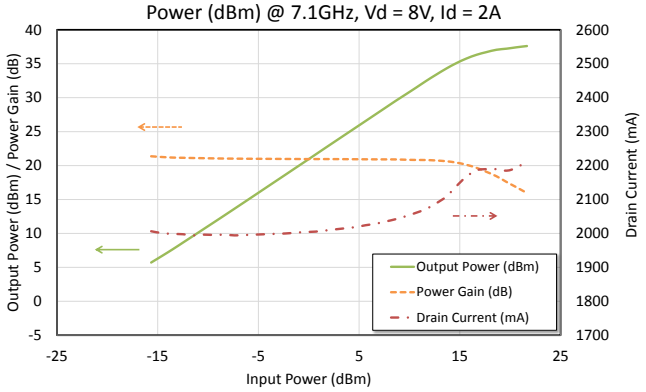


Output IP3 (dBm) vs. Freq (GHz), Vd = 8V, Id = 2A

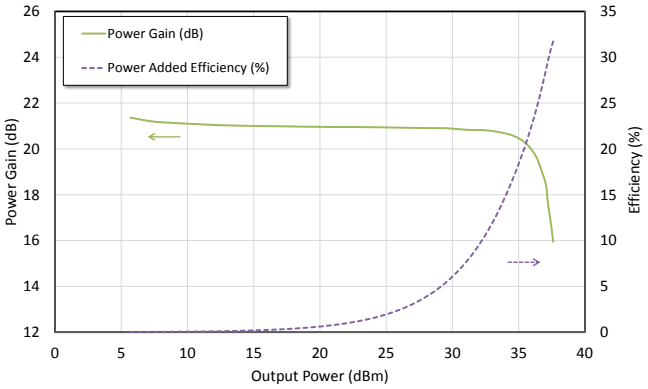


Typical Performance Curves: V_D = 8 V, I_{DQ} = 2 A, V_G = -1.05 ~ -0.95 V, T_A = +25°C

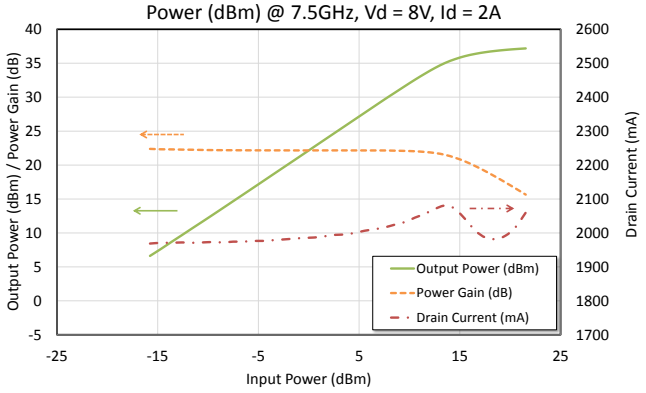
Output Power (dBm) and Power Gain vs. Input Power (dBm) @ 7.1GHz, Vd = 8V, Id = 2A



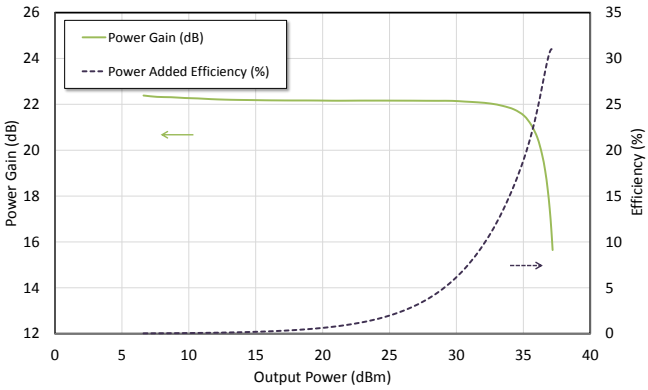
Pwr Gain/PAE @ 7.1GHz vs. OP Pwr (dBm), Vd = 8V, Id = 2A



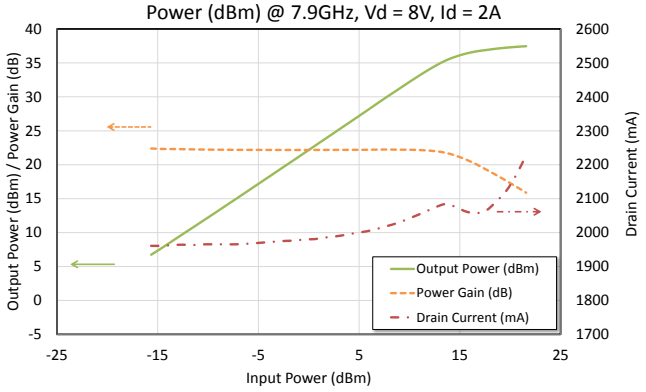
Output Power (dBm) and Power Gain vs. Input Power (dBm) @ 7.5GHz, Vd = 8V, Id = 2A



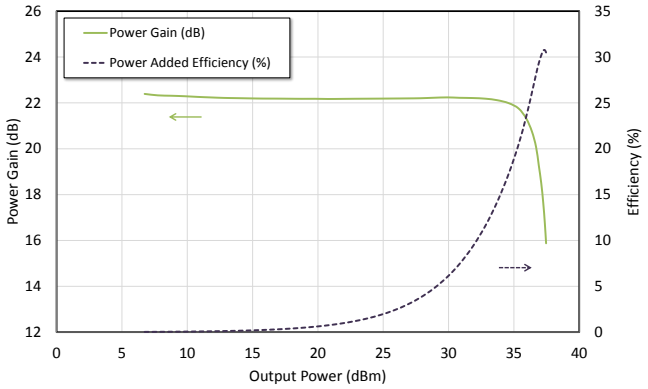
Pwr Gain/PAE @ 7.5GHz vs. OP Pwr (dBm), Vd = 8V, Id = 2A



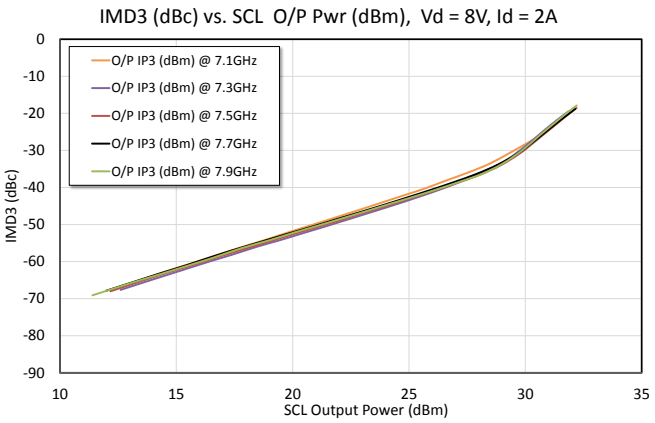
Output Power (dBm) and Power Gain vs. Input Power (dBm) @ 7.9GHz, Vd = 8V, Id = 2A

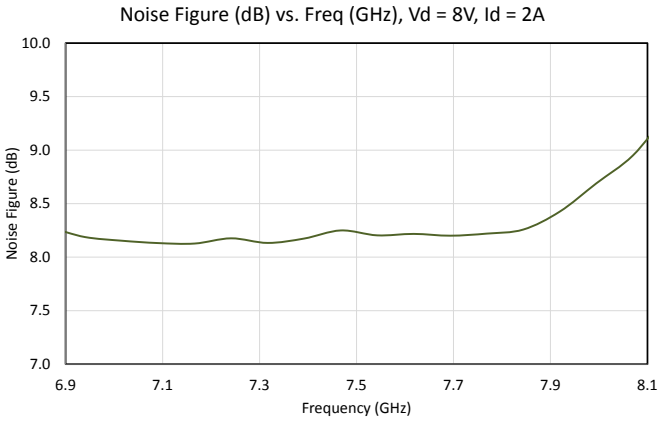


Pwr Gain/PAE @ 7.9GHz vs. OP Pwr (dBm), Vd = 8V, Id = 2A

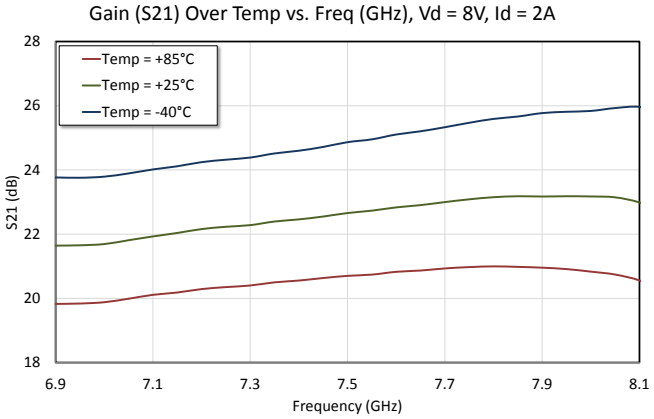


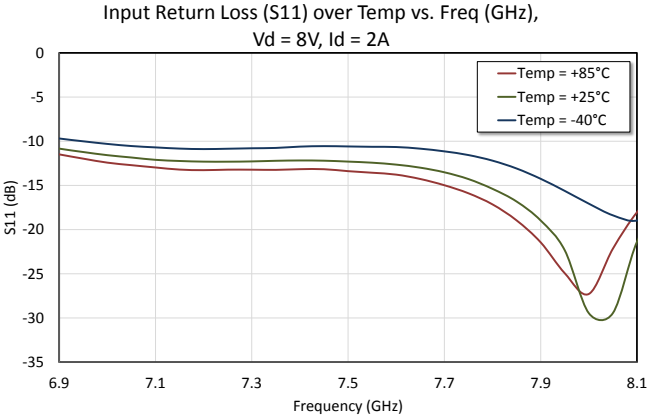
Typical Performance Curves: V_D = 8 V, I_{DQ} = 2 A, V_G = -1.05 ~ -0.95 V, T_A = +25°C

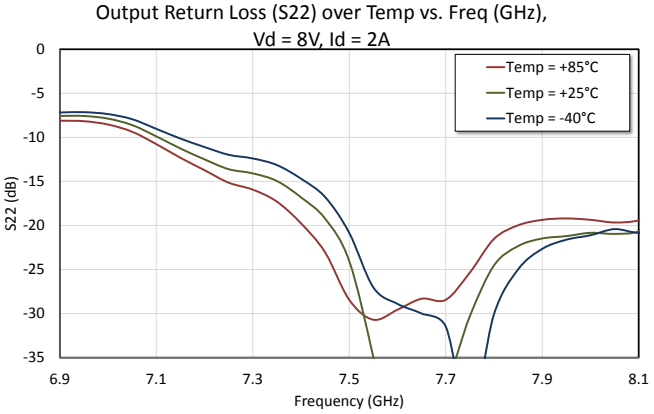


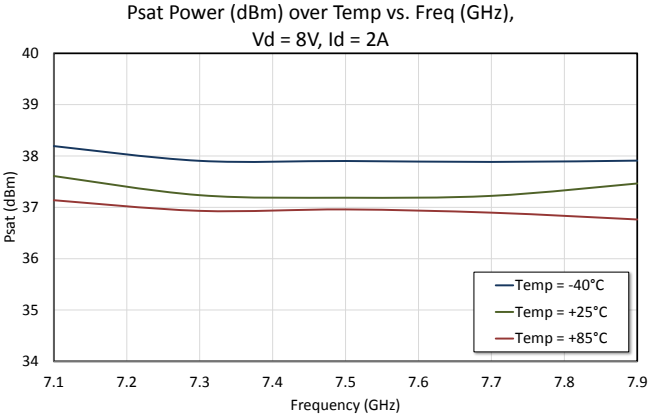


Typical Performance Curves: V_D = 8 V, I_{DQ} = 2 A, V_G = -1.05 ~ -0.95 V, T_A = -40°C ~ +85°C



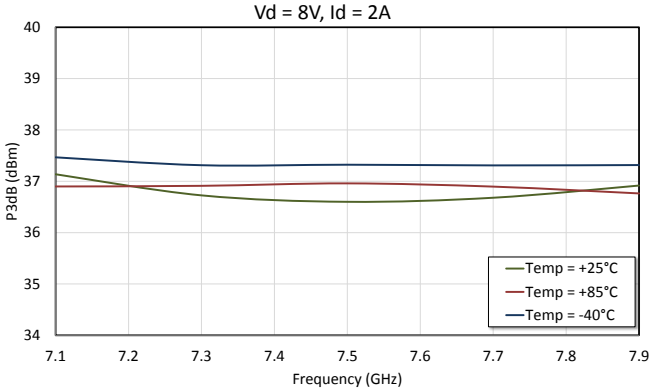




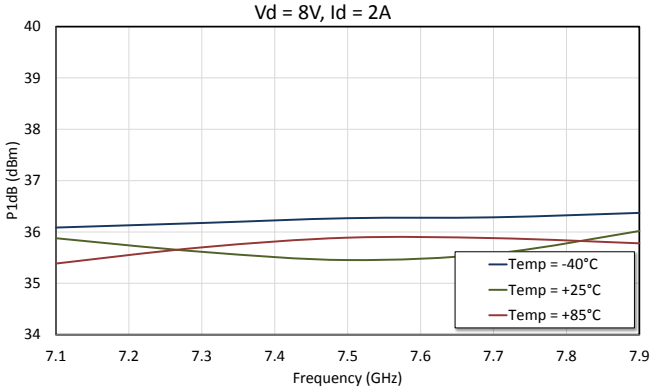


Typical Performance Curves: V_D = 8 V, I_{DQ} = 2 A, V_G = -1.05 ~ -0.95 V, T_A = -40°C ~ +85°C

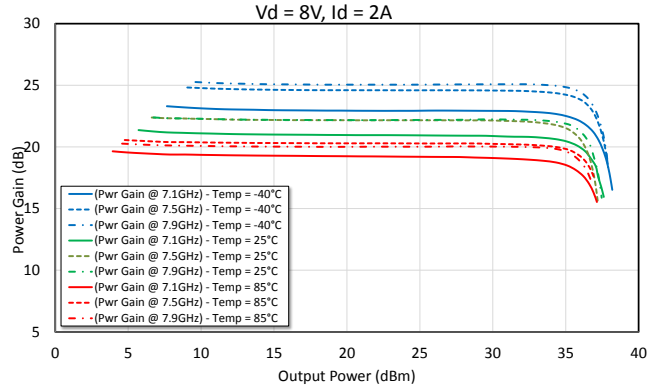
P3dB Power (dBm) over Temp vs. Freq (GHz), Vd = 8V, Id = 2A



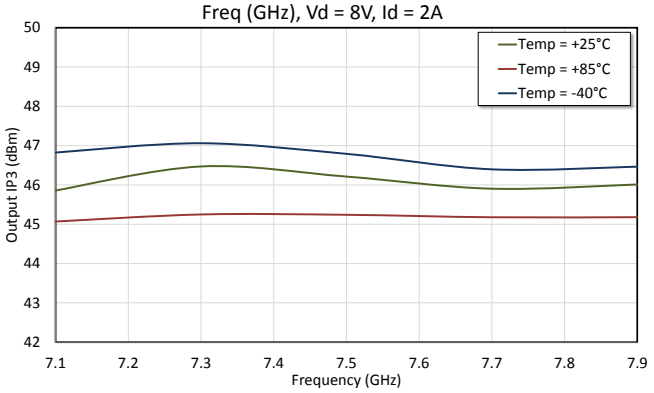
P1dB Power (dBm) over Temp vs. Freq (GHz), Vd = 8V, Id = 2A



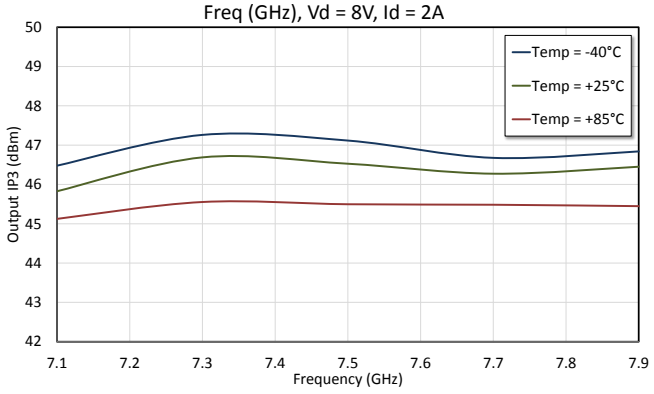
Power Gain (dB) over Temp vs. Output Power (dBm), Vd = 8V, Id = 2A



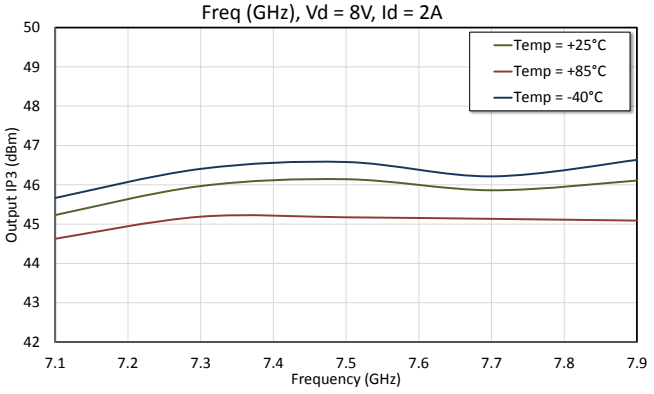
Output IP3 at 17.5dBm SCL O/P Pwr (dBm) over Temp vs. Freq (GHz), Vd = 8V, Id = 2A



Output IP3 at 25.5dBm SCL O/P Pwr (dBm) over Temp vs. Freq (GHz), Vd = 8V, Id = 2A

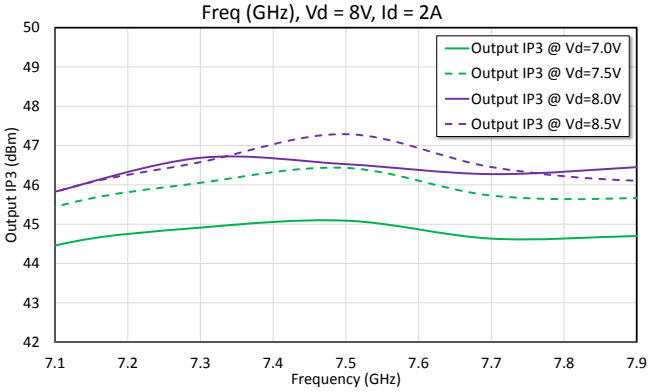


Output IP3 at 28.5dBm SCL O/P Pwr (dBm) over Temp vs. Freq (GHz), Vd = 8V, Id = 2A

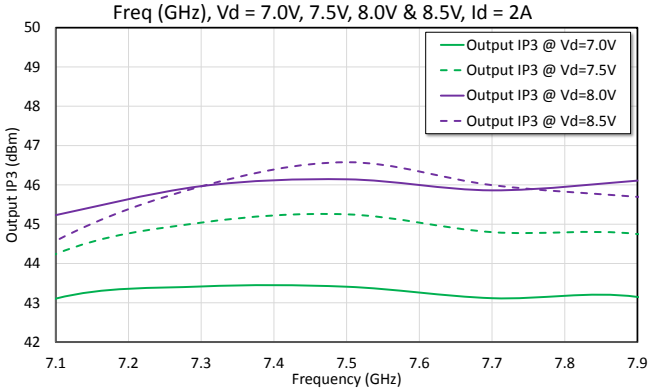


Typical Performance Curves: V_D = Various, I_{DQ} = 2 A, V_G = -1.05 ~ -0.95 V, T_A = +25°C

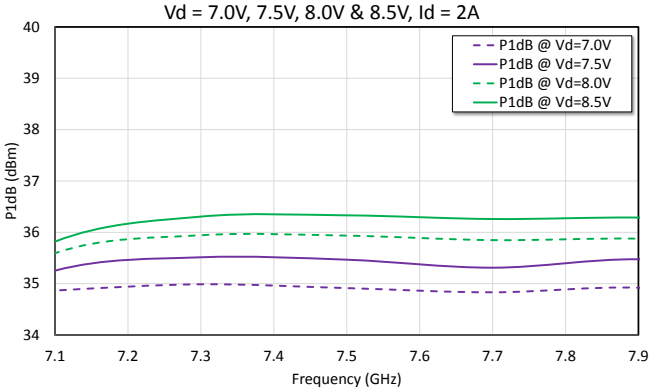
Output IP3 at 25.5dBm SCL O/P Pwr (dBm) over Temp vs. Freq (GHz), Vd = 8V, Id = 2A



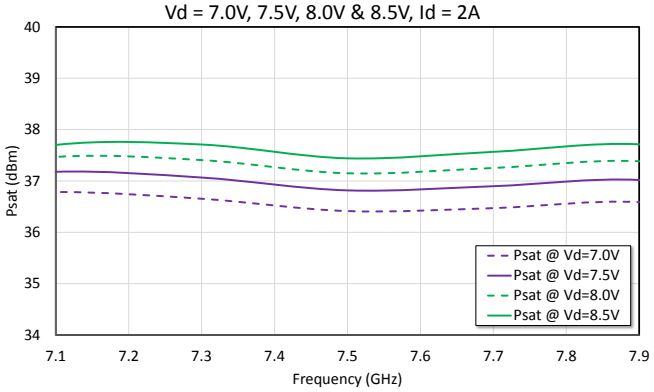
Output IP3 at 28.5dBm SCL O/P Pwr (dBm) over Temp vs. Freq (GHz), Vd = 7.0V, 7.5V, 8.0V & 8.5V, Id = 2A



P1dB Power (dBm) over Temp vs. Freq (GHz), Vd = 7.0V, 7.5V, 8.0V & 8.5V, Id = 2A

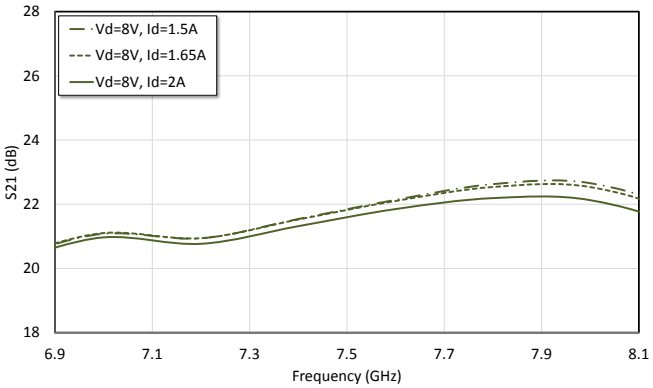


Psat Power (dBm) over Temp vs. Freq (GHz), Vd = 7.0V, 7.5V, 8.0V & 8.5V, Id = 2A

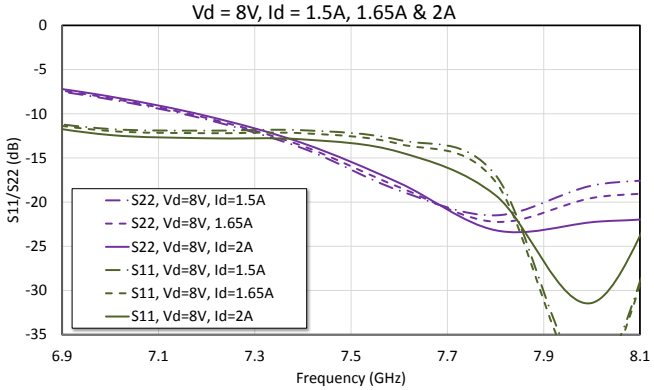


Typical Performance Curves: V_D = Various, I_{DQ} = 1.5 A, 1.65 A, 2.0 A, V_G = -1.15 ~ -0.95 V, T_A = +25°C

Gain (S21) vs. Freq (GHz), Vd = 8V, Id = 1.5A, 1.65A & 2A

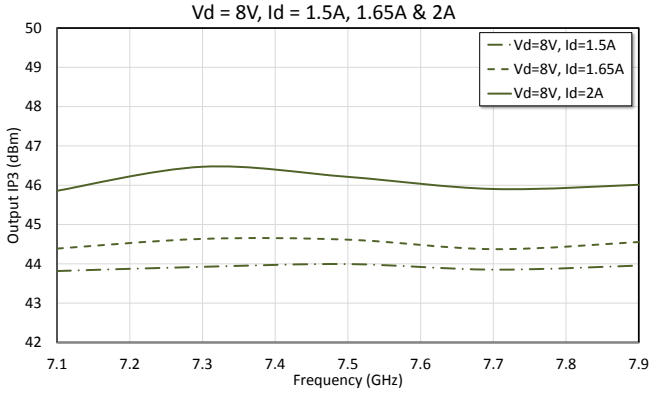


IP/OP Return Loss (S11/S22) over Temp vs. Freq (GHz), Vd = 8V, Id = 1.5A, 1.65A & 2A

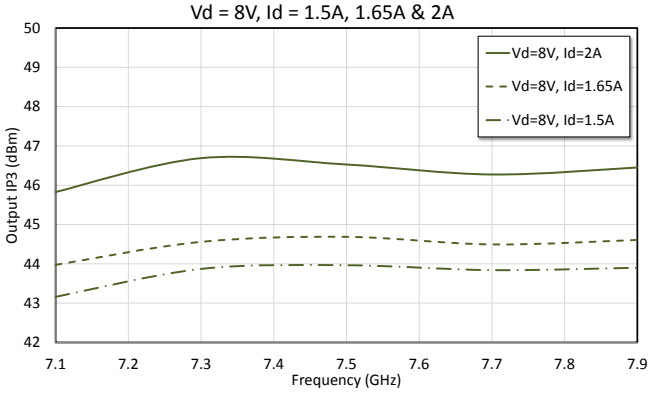


Typical Performance Curves:
V_D = Various, I_{DQ} = 1.5 A, 1.65 A, 2.0 A, V_G = -1.15 ~ -0.95 V, T_A = +25°C

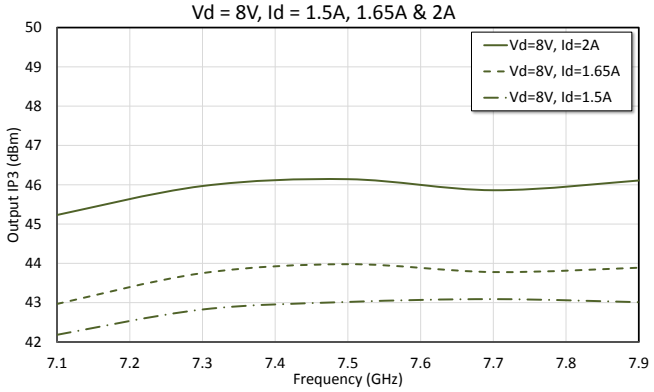
Output IP3 at 17.5dBm SCL O/P Pwr (dBm) vs. Freq (GHz),
Vd = 8V, Id = 1.5A, 1.65A & 2A



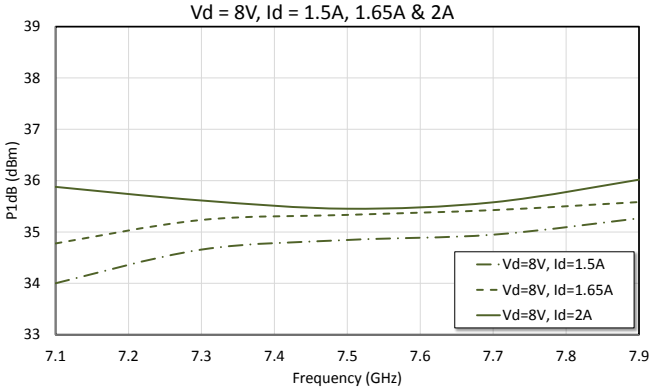
Output IP3 at 25.5dBm SCL O/P Pwr (dBm) vs. Freq (GHz),
Vd = 8V, Id = 1.5A, 1.65A & 2A



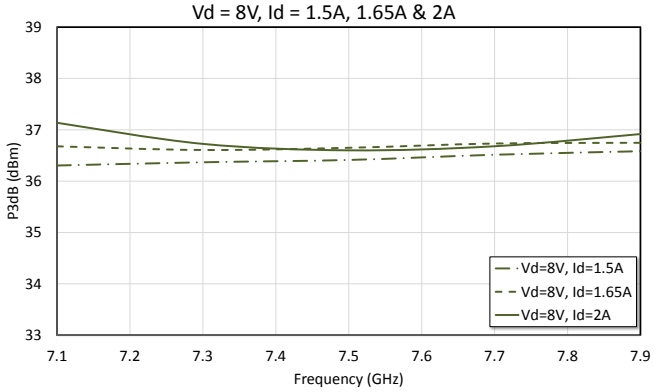
Output IP3 at 28.5dBm SCL O/P Pwr (dBm) vs. Freq (GHz),
Vd = 8V, Id = 1.5A, 1.65A & 2A



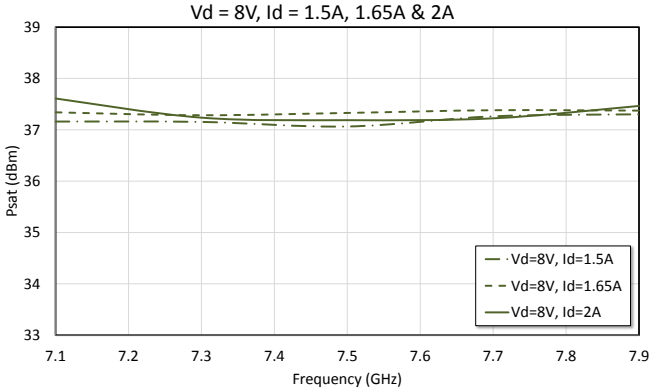
P1dB Power (dBm) vs. Freq (GHz),
Vd = 8V, Id = 1.5A, 1.65A & 2A



P3dB Power (dBm) vs. Freq (GHz),
Vd = 8V, Id = 1.5A, 1.65A & 2A

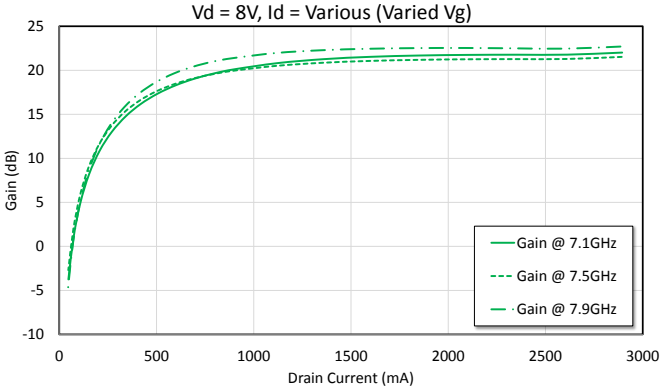


Psat Power (dBm) vs. Freq (GHz),
Vd = 8V, Id = 1.5A, 1.65A & 2A

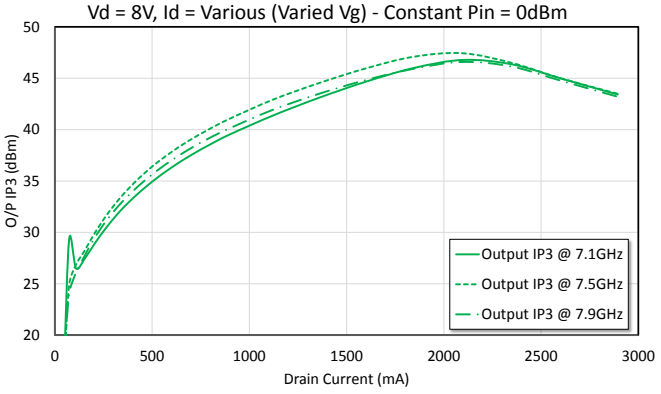


Typical Performance Curves: V_D = 8 V, I_{DQ} = Various, V_G = -0.9 ~ 1.65 V, T_A = +25°C

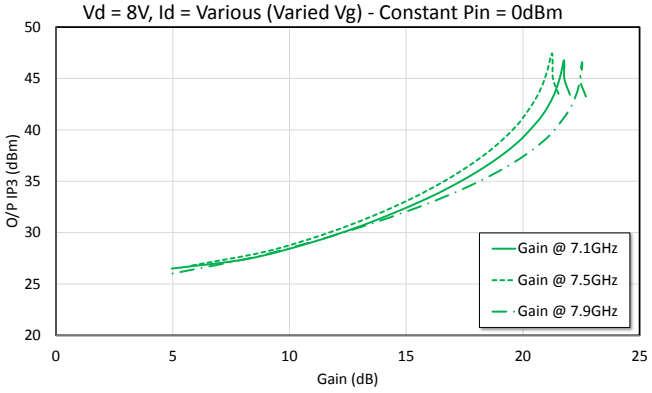
Gain (dB) over Various Frequencies vs. Drain Current (Id),
Vd = 8V, Id = Various (Varied Vg)



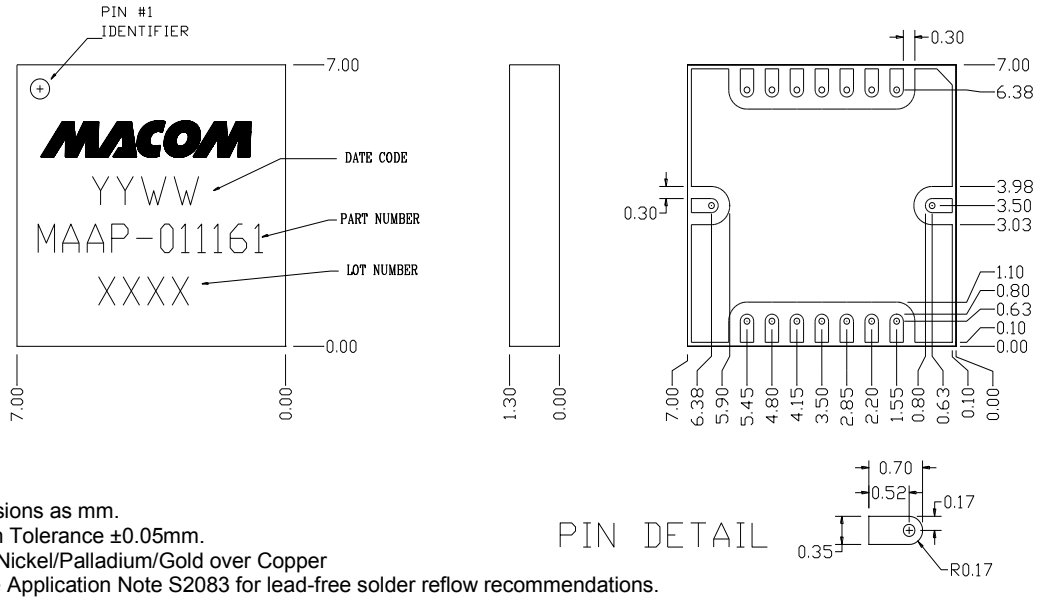
O/P IP3 (dBm) @ Various Frequencies vs. Drain Current (Id),
Vd = 8V, Id = Various (Varied Vg) - Constant Pin = 0dBm



O/P IP3 (dB) @ Various Frequencies vs. Gain (dB),
Vd = 8V, Id = Various (Varied Vg) - Constant Pin = 0dBm



Lead Free 7 mm Laminate Package (16 pin)†



1. All Dimensions as mm.
2. Dimension Tolerance ±0.05mm.
3. Plating is Nickel/Palladium/Gold over Copper
4. Reference Application Note S2083 for lead-free solder reflow recommendations.

† Meets JEDEC moisture sensitivity level 3 requirements.

Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001
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Данный компонент на территории Российской Федерации

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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